# SCR/SCR and SCR/Diode (MAGN-A-PAK Power Modules), 230 A



MAGN-A-PAK

## FEATURES

- High voltage
- Electrically isolated base plate
- 3500 $V_{RMS}$ isolating voltage
- Industrial standard package
- Simplified mechanical designs, rapid assembly
- High surge capability
- Large creepage distances
- UL approved file E78996
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT

| PRIMARY CHARACTERISTICS | |
|---|---|
| $I_{T(AV)}$ | 230 A |
| Type | Modules - thyristor, standard |
| Package | MAGN-A-PAK |

## DESCRIPTION

This VSK series of MAGN-A-PAK modules uses high voltage power thyristor/thyristor and thyristor/diode in seven basic configurations. The semiconductors are electrically isolated from the metal base, allowing common heatsinks and compact assemblies to be built. They can be interconnected to form single phase or three phase bridges or as AC-switches when modules are connected in anti-parallel mode. These modules are intended for general purpose applications such as battery chargers, welders, motor drives, UPS, etc.

| MAJOR RATINGS AND CHARACTERISTICS | | | |
|---|---|---|---|
| SYMBOL | CHARACTERISTICS | VALUES | UNITS |
| $I_{T(AV)}$ | 85 °C | 230 | A |
| $I_{T(RMS)}$ | | 510 | |
| $I_{TSM}$ | 50 Hz | 7500 | |
| | 60 Hz | 7850 | |
| $I^2t$ | 50 Hz | 280 | $kA^2s$ |
| | 60 Hz | 260 | |
| $I^2\sqrt{t}$ | | 280 | $kA^2\sqrt{s}$ |
| $V_{DRM}/V_{RRM}$ | | 800 to 2000 | V |
| $T_J$ | Range | -40 to +130 | °C |

## ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS | | | | |
|---|---|---|---|---|
| TYPE NUMBER | VOLTAGE CODE | $V_{RRM}/V_{DRM}$, MAXIMUM REPETITIVE PEAK REVERSE AND OFF-STATE BLOCKING VOLTAGE V | $V_{RSM}$, MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V | $I_{RRM}/I_{DRM}$ AT 130 °C MAXIMUM mA |
| VS-VSK.230- | 08 | 800 | 900 | 50 |
| | 12 | 1200 | 1300 | |
| | 16 | 1600 | 1700 | |
| | 18 | 1800 | 1900 | |
| | 20 | 2000 | 2100 | |



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## ON-STATE CONDUCTION

| PARAMETER | SYMBOL | TEST CONDITIONS | | | VALUES | UNITS |
|---|---|---|---|---|---|---|
| Maximum average on-state current at case temperature | $I_{T(AV)}$ | 180° conduction, half sine wave | | | 230 | A |
| | | | | | 85 | °C |
| Maximum RMS on-state current | $I_{T(RMS)}$ | As AC switch | | | 510 | A |
| Maximum peak, one-cycle on-state non-repetitive, surge current | $I_{TSM}$ | t = 10 ms | No voltage reapplied | Sinusoidal half wave, initial $T_J = T_J$ maximum | 7500 | |
| | | t = 8.3 ms | | | 7850 | |
| | | t = 10 ms | 100 % $V_{RRM}$ reapplied | | 6300 | |
| | | t = 8.3 ms | | | 6600 | |
| Maximum $I^2t$ for fusing | $I^2t$ | t = 10 ms | No voltage reapplied | | 280 | $kA^2s$ |
| | | t = 8.3 ms | | | 256 | |
| | | t = 10 ms | 100 % $V_{RRM}$ reapplied | | 198 | |
| | | t = 8.3 ms | | | 181 | |
| Maximum $I^2\sqrt{t}$ for fusing | $I^2\sqrt{t}$ | t = 0.1 ms to 10 ms, no voltage reapplied | | | 2800 | $kA^2\sqrt{s}$ |
| Low level value or threshold voltage | $V_{T(TO)1}$ | (16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum | | | 1.03 | V |
| High level value of threshold voltage | $V_{T(TO)2}$ | (I > π x $I_{T(AV)}$), $T_J = T_J$ maximum | | | 1.07 | |
| Low level value on-state slope resistance | $r_{t1}$ | (16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum | | | 0.77 | mΩ |
| High level value on-state slope resistance | $r_{t2}$ | (I > π x $I_{T(AV)}$), $T_J = T_J$ maximum | | | 0.73 | |
| Maximum on-state voltage drop | $V_{TM}$ | $I_{TM}$ = π x $I_{T(AV)}$, $T_J = T_J$ maximum, 180° conduction, average power = $V_{T(TO)}$ x $I_{T(AV)}$ + $r_f$ x $(I_{T(RMS)})^2$ | | | 1.59 | V |
| Maximum holding current | $I_H$ | Anode supply = 12 V, initial $I_T$ = 30 A, $T_J$ = 25 °C | | | 500 | mA |
| Maximum latching current | $I_L$ | Anode supply = 12 V, resistive load = 1 Ω, gate pulse: 10 V, 100 µs, $T_J$ = 25 °C | | | 1000 | |

## SWITCHING

| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
|---|---|---|---|---|
| Typical delay time | $t_d$ | $T_J$ = 25 °C, gate current = 1 A $dI_g/dt$ = 1 A/µs, $V_d$ = 0.67 % $V_{DRM}$ | 1.0 | µs |
| Typical rise time | $t_r$ | | 2.0 | |
| Typical turn-off time | $t_q$ | $I_{TM}$ = 300 A; dI/dt = 15 A/µs; $T_J = T_J$ maximum; $V_R$ = 50 V; dV/dt = 20 V/µs; gate 0 V, 100 Ω | 50 to 150 | |

## BLOCKING

| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
|---|---|---|---|---|
| Maximum peak reverse and off-state leakage current | $I_{RRM}$, $I_{DRM}$ | $T_J = T_J$ maximum | 50 | mA |
| RMS insulation voltage | $V_{INS}$ | 50 Hz, circuit to base, all terminals shorted, 25 °C, 1 s | 3000 | V |
| Critical rate of rise of off-state voltage | dV/dt | $T_J = T_J$ maximum, exponential to 67 % rated $V_{DRM}$ | 1000 | V/µs |

## TRIGGERING

| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
|---|---|---|---|---|---|
| Maximum peak gate power | $P_{GM}$ | $t_p \leq 5$ ms, $T_J = T_J$ maximum | | 10.0 | W |
| Maximum average gate power | $P_{G(AV)}$ | f = 50 Hz, $T_J = T_J$ maximum | | 2.0 | |
| Maximum peak gate current | + $I_{GM}$ | $t_p \leq 5$ ms, $T_J = T_J$ maximum | | 3.0 | A |
| Maximum peak negative gate voltage | - $V_{GT}$ | $t_p \leq 5$ ms, $T_J = T_J$ maximum | | 5.0 | V |
| Maximum required DC gate voltage to trigger | $V_{GT}$ | $T_J$ = -40 °C | Anode supply = 12 V, resistive load; Ra = 1 Ω | 4.0 | |
| | | $T_J$ = 25 °C | | 3.0 | |
| | | $T_J = T_J$ maximum | | 2.0 | |
| Maximum required DC gate current to trigger | $I_{GT}$ | $T_J$ = - 40 °C | Anode supply = 12 V, resistive load; Ra = 1 Ω | 350 | mA |
| | | $T_J$ = 25 °C | | 200 | |
| | | $T_J = T_J$ maximum | | 100 | |
| Maximum gate voltage that will not trigger | $V_{GD}$ | $T_J = T_J$ maximum, rated $V_{DRM}$ applied | | 0.25 | V |
| Maximum gate current that will not trigger | $I_{GD}$ | $T_J = T_J$ maximum, rated $V_{DRM}$ applied | | 10.0 | mA |
| Maximum rate of rise of turned-on current | dI/dt | $T_J = T_J$ maximum, $I_{TM}$ = 400 A, rated $V_{DRM}$ applied | | 500 | A/µs |


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| THERMAL AND MECHANICAL SPECIFICATIONS | | | | |
|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | **VALUES** | **UNITS** |
| Junction operating temperature range | $T_J$ | | -40 to +130 | °C |
| Storage temperature range | $T_{Stg}$ | | -40 to +150 | |
| Maximum thermal resistance, junction to case per junction | $R_{thJC}$ | DC operation | 0.125 | K/W |
| Typical thermal resistance, case to heatsink per module | $R_{thCS}$ | Mounting surface flat, smooth, and greased | 0.02 | |
| Mounting torque ± 10 % — MAGN-A-PAK to heatsink | | A mounting compound is recommended and the torque should be rechecked after a period of about 3 h to allow for the spread of the compound. | 4 to 6 | Nm |
| Mounting torque ± 10 % — busbar to MAGN-A-PAK | | | | |
| Approximate weight | | | 500 | g |
| | | | 17.8 | oz. |
| Case style | | | MAGN-A-PAK | |

| ΔR CONDUCTION PER JUNCTION | | | | | | | | | | | |
|---|---|---|---|---|---|---|---|---|---|---|---|
| **DEVICES** | **SINUSOIDAL CONDUCTION AT $T_J$ MAXIMUM** | | | | | **RECTANGULAR CONDUCTION AT $T_J$ MAXIMUM** | | | | | **UNITS** |
| | **180°** | **120°** | **90°** | **60°** | **30°** | **180°** | **120°** | **90°** | **60°** | **30°** | |
| VSK.230- | 0.009 | 0.010 | 0.010 | 0.020 | 0.032 | 0.007 | 0.011 | 0.015 | 0.020 | 0.033 | K/W |

**Note**

- Table shows the increment of thermal resistance $R_{thJC}$ when devices operate at different conduction angles than DC

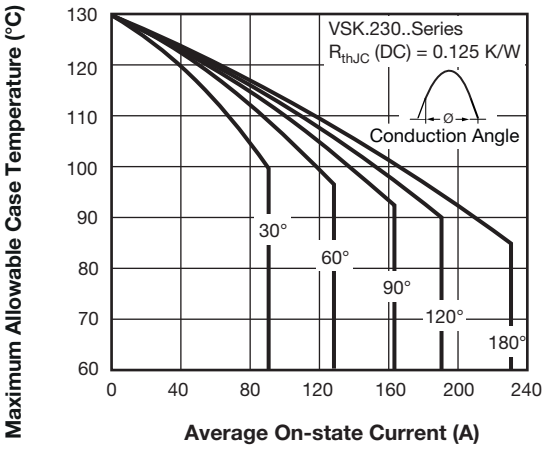



Fig. 1 - Current Ratings Characteristics

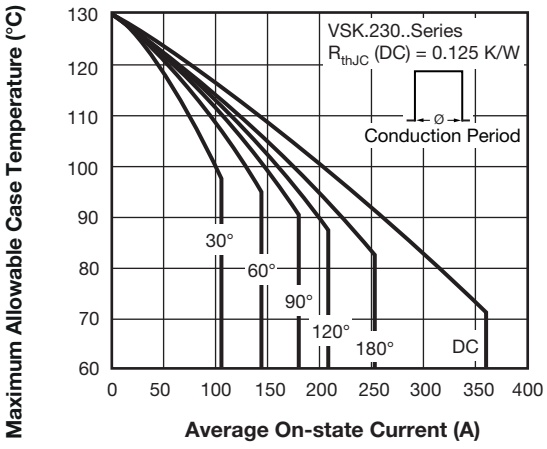



Fig. 2 - Current Ratings Characteristics



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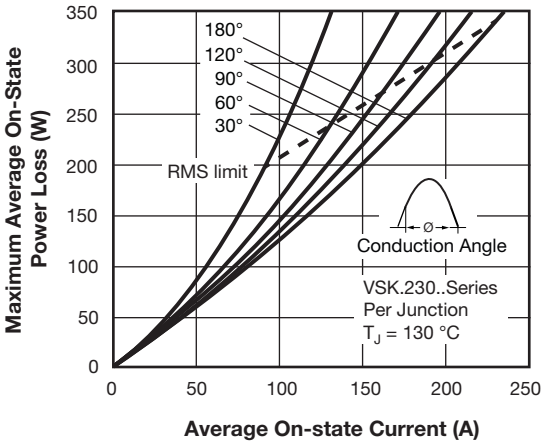



Fig. 3 - On-State Power Loss Characteristics

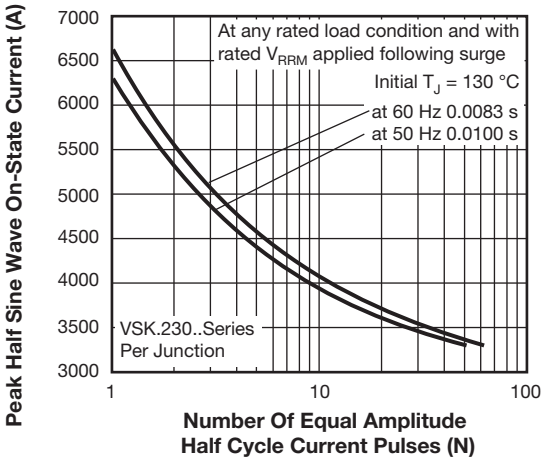



Fig. 5 - Maximum Non-Repetitive Surge Current

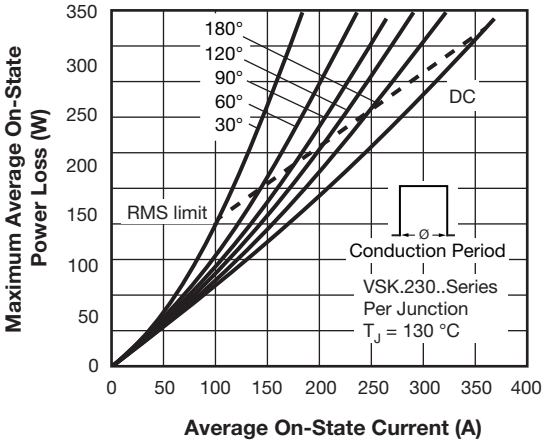



Fig. 4 - On-State Power Loss Characteristics

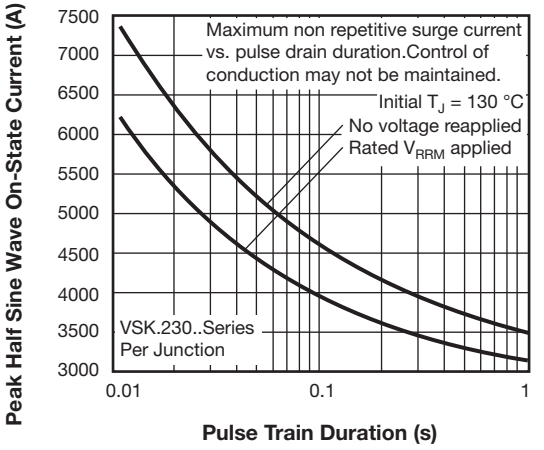



Fig. 6 - Maximum Non-Repetitive Surge Current

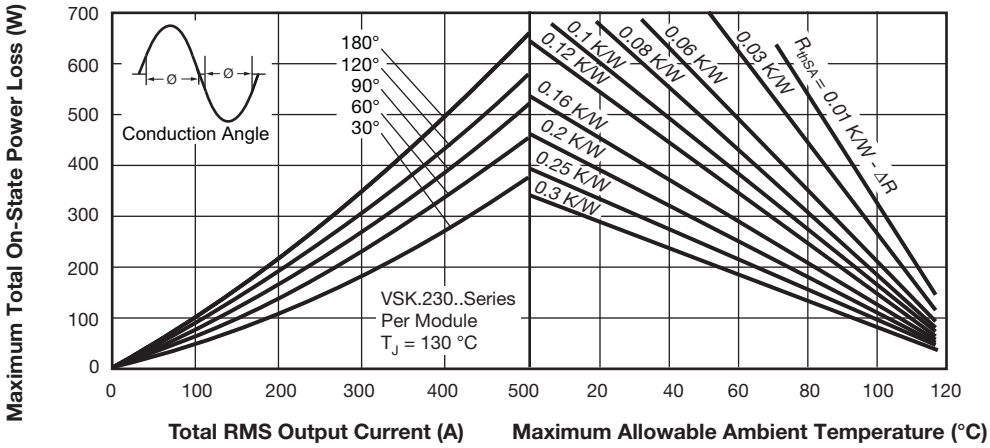



Fig. 7 - On-State Power Loss Characteristics


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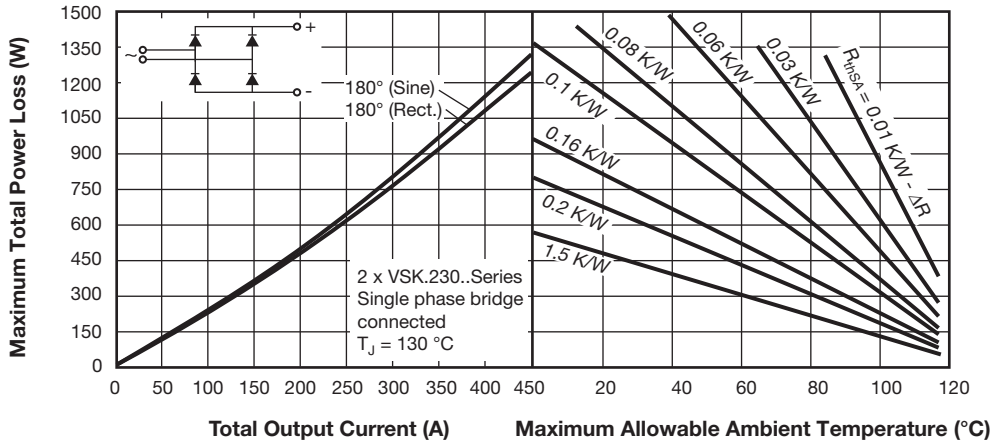



Fig. 8 - On-State Power Loss Characteristics

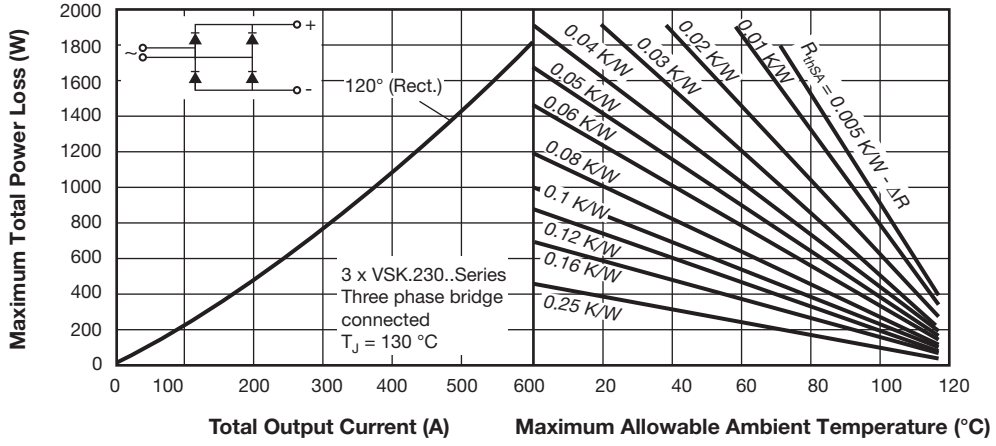



Fig. 9 - On-State Power Loss Characteristics

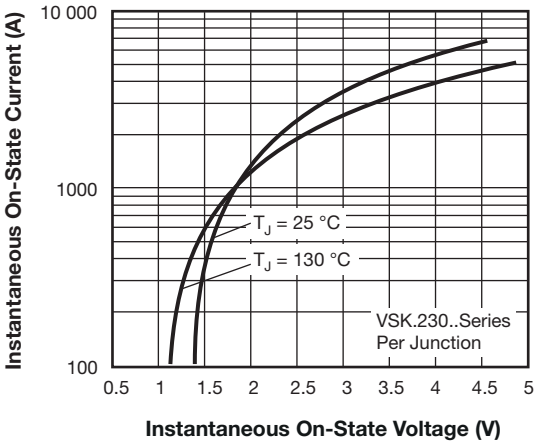



Fig. 10 - On-State Voltage Drop Characteristics

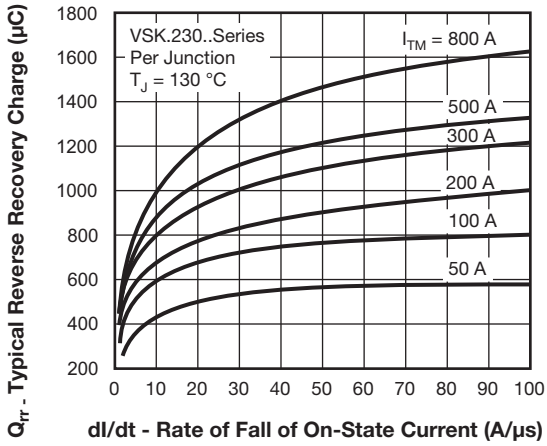



Fig. 11 - Reverse Recovery Charge Characteristics


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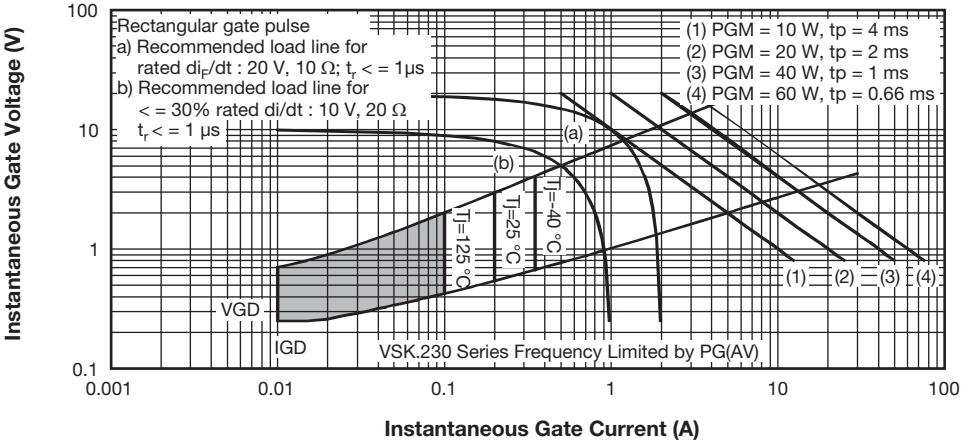



Fig. 12 - Gate Characteristics

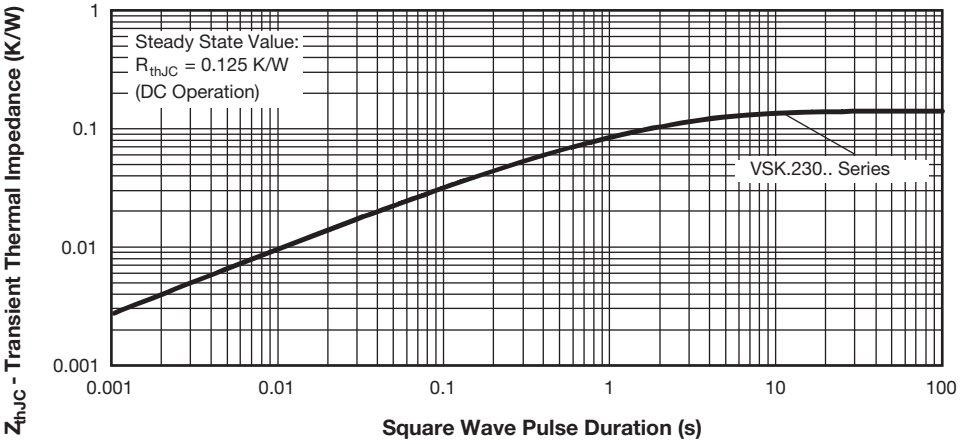



Fig. 13 - Thermal Impedance $Z_{thJC}$ Characteristics

## ORDERING INFORMATION TABLE

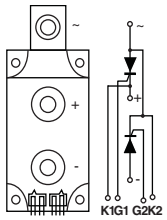
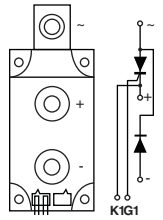
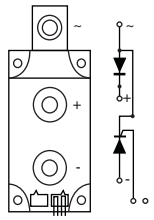
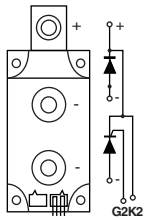
| Device code | VS-VS | KT | 230 | - | 20 | PbF |
|---|---|---|---|---|---|---|
| | 1 | 2 | 3 | | 4 | 5 |

- **1** - Vishay Semiconductors product
- **2** - Circuit configuration (see dimensions - link at the end of datasheet)
- **3** - Current rating
- **4** - Voltage code x 100 = $V_{RRM}$ (see Voltage Ratings table)
- **5** - • None = standard production
  • PbF = lead (Pb)-free

**Note**

- To order the optional hardware go to www.vishay.com/doc?95172


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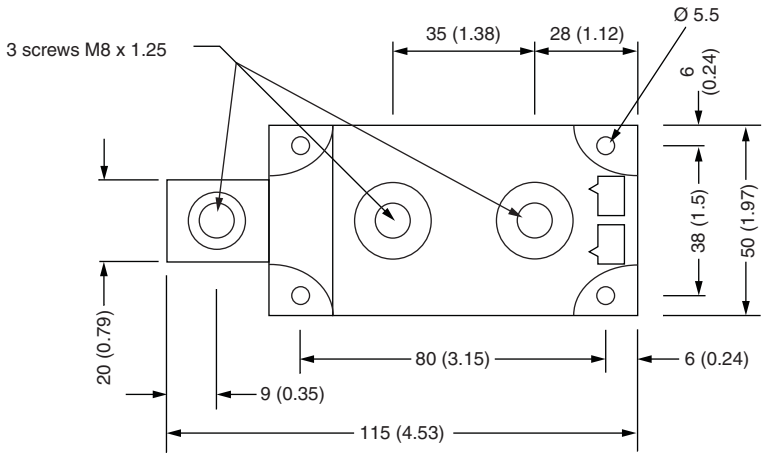
| CIRCUIT CONFIGURATION | | |
|---|---|---|
| **CIRCUIT DESCRIPTION** | **CIRCUIT CONFIGURATION CODE** | **CIRCUIT DRAWING** |
| Two SCRs doubler circuit | KT | **VSKT...**   Available 800 V: contact factory for different requirements |
| SCR/diode doubler circuit, positive control | KH | **VSKH...**   Available 800 V: contact factory for different requirements |
| SCR/diode doubler circuit, negative control | KL | **VSKL...**   Available 800 V: contact factory for different requirements |
| Two SCRs common cathodes | KK | **VSKK...**   Available 800 V: contact factory for different requirements |

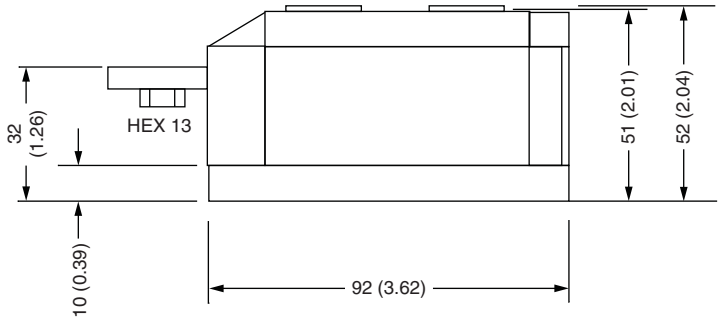
| LINKS TO RELATED DOCUMENTS | |
|---|---|
| Dimensions | www.vishay.com/doc?95086 |


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# MAGN-A-PAK

**DIMENSIONS** in millimeters (inches)




**Notes**

- Dimensions are nominal
- Full engineering drawings are available on request
- UL identification number for gate and cathode wire: UL 1385
- UL identification number for package: UL 94 V-0

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